N- and P-Channel 20-V (D-S) MOSFET

CHARACTERISTICS

- N- and P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

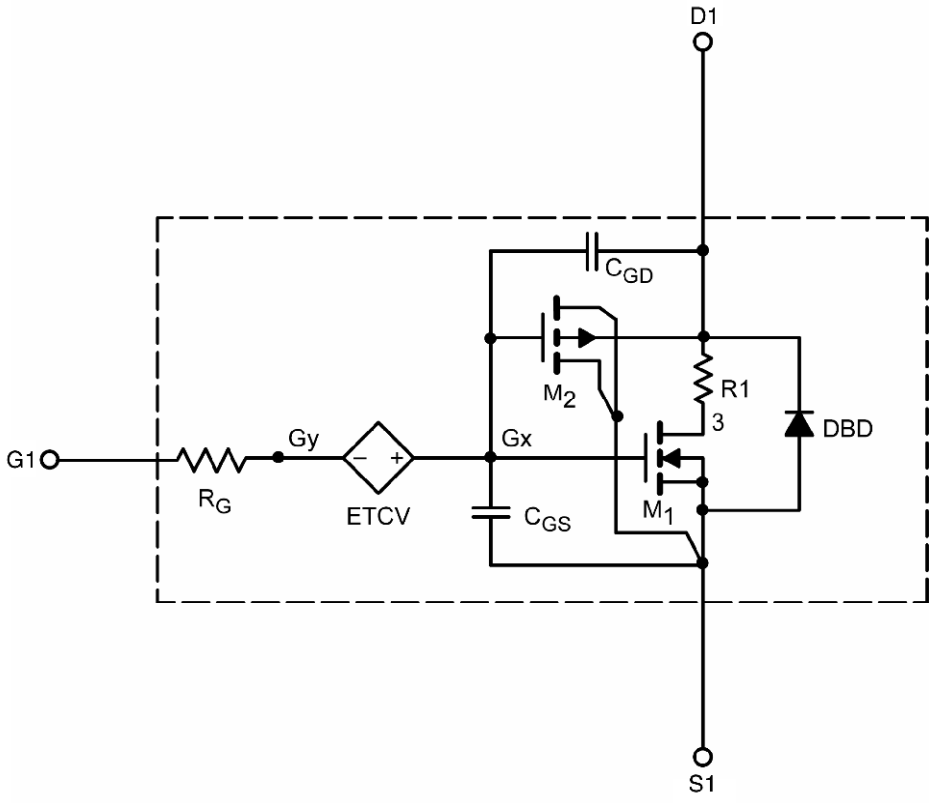
DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n- and p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 5 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC

N-Channel MOSFET



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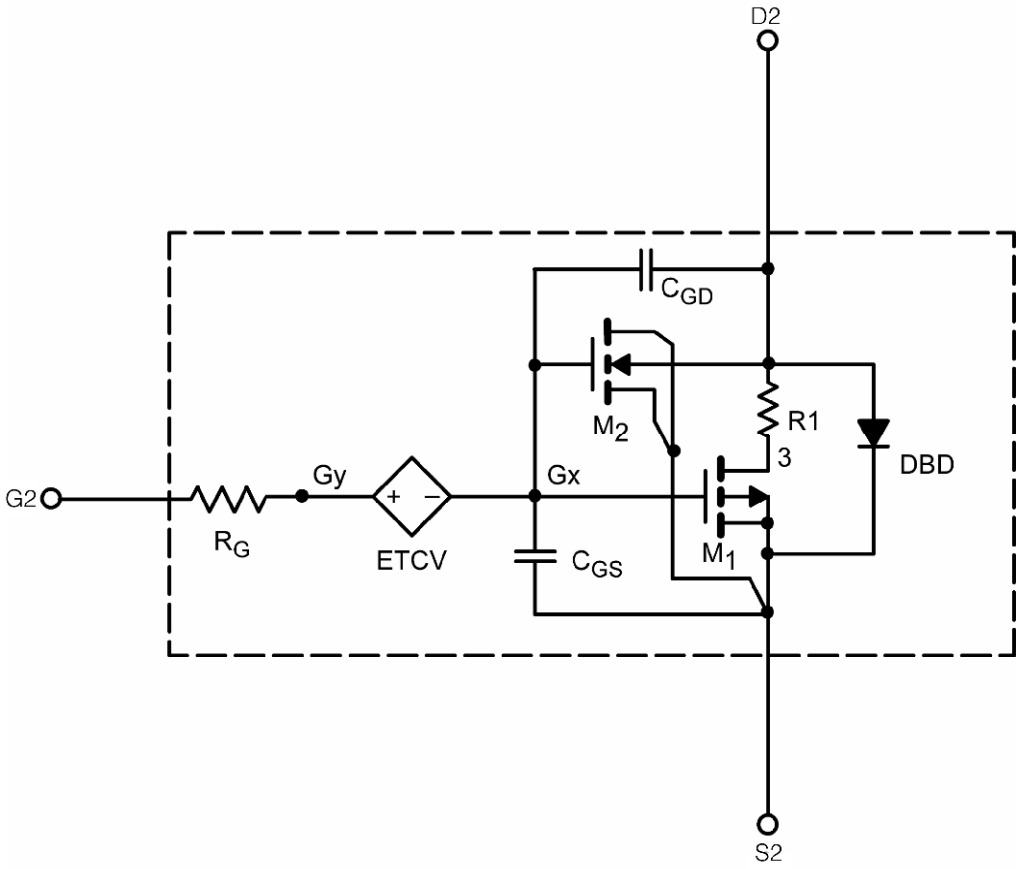
SUBCIRCUIT MODEL SCHEMATIC
P-Channel MOSFET



SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Condition**		**Simulated Data**	**Measured Data**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	0.60		
		V_{DS} = V_{GS}, I_D = - 250 µA	P-Ch	0.60		
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 6 A	N-Ch	0.029	0.030	Ω
		V_{GS} = - 4.5 V, I_D = - 3.1 A	P-Ch	0.083	0.083	
		V_{GS} = 2.5 V, I_D = 5.6 A	N-Ch	0.034	0.034	
		V_{GS} = - 2.5 V, I_D = - 2.8 A	P-Ch	0.10	0.10	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 6 A	N-Ch	24	22.4	S
		V_{DS} = - 10 V, I_D = - 3.1 A	P-Ch	9.7	9.5	
Diode Forward Voltage[a]	V_{SD}	I_S = 4.8 A, V_{GS} = 0 V	N-Ch	0.76	0.80	V
		I_S = - 2.4 A, V_{GS} = 0 V	P-Ch	0.85	- 0.80	
Dynamic[b]						
Input Capacitance	C_{iss}	N-Channel V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz P-Channel V_{DS} = - 10 V, V_{GS} = 0 V, f = 1 MHz	N-Ch	640	632	pF
			P-Ch	462	455	
Output Capacitance	C_{oss}		N-Ch	90	80	
			P-Ch	83	70	
Reverse Transfer Capacitance	C_{rss}		N-Ch	40	40	
			P-Ch	64	54	
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 5 V, I_D = 6 A	N-Ch	5.5	7.5	nC
		V_{DS} = –10 V, V_{GS} = –5 V, I_D = –3.1 A	P-Ch	5.6	7	
		N-Channel V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 6 A P-Channel V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 3.1 A	N-Ch	5	6.5	
			P-Ch	5.1	6.2	
Gate-Source Charge	Q_{gs}		N-Ch	1.1	1.1	
			P-Ch	0.85	0.85	
Gate-Source Charge	Q_{gs}		N-Ch	0.90	0.90	
			P-Ch	1.75	1.75	

Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

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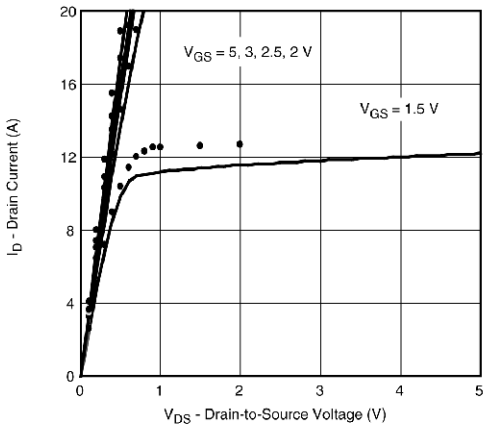
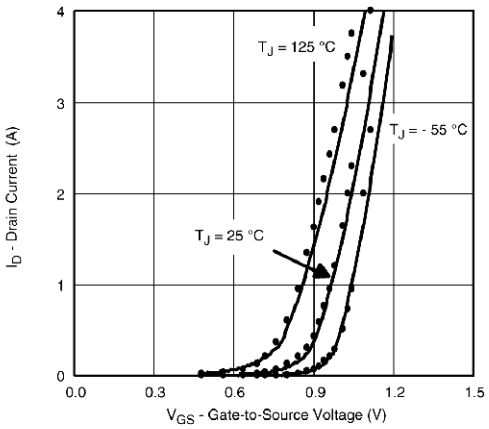
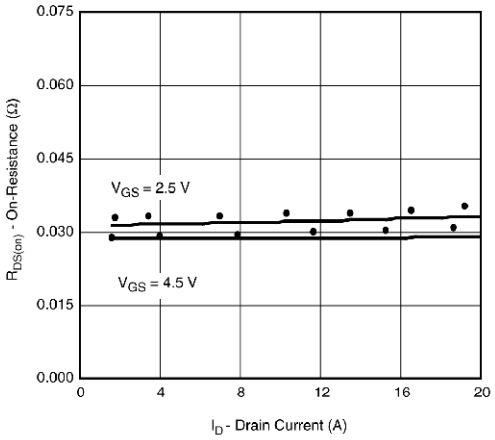
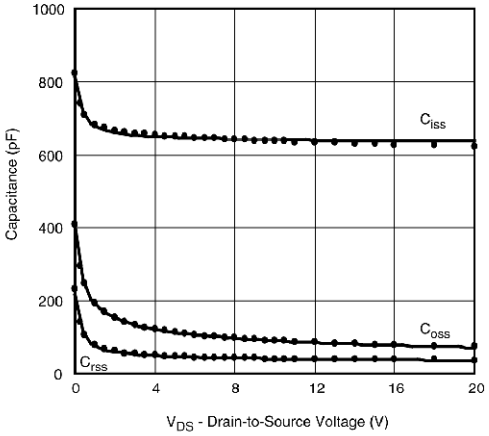
COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C UNLESS OTHERWISE NOTED)

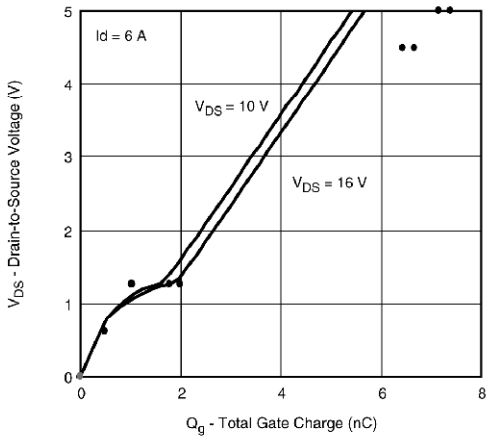
N-Channel MOSFET

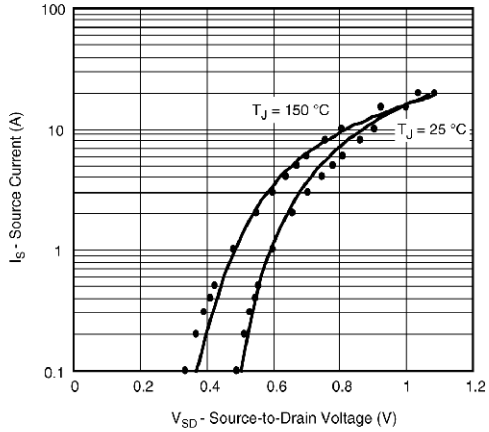








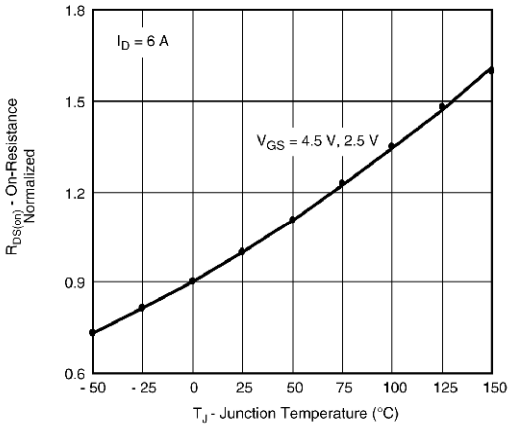


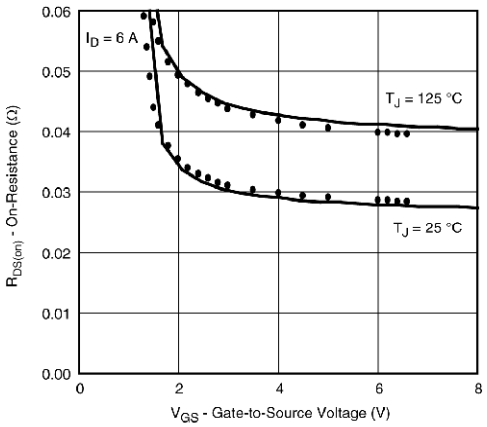


Note: Dots and squares represent measured data.

COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C UNLESS OTHERWISE NOTED)

N-Channel MOSFET





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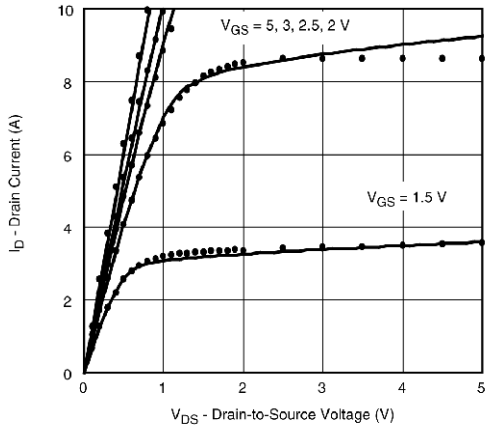
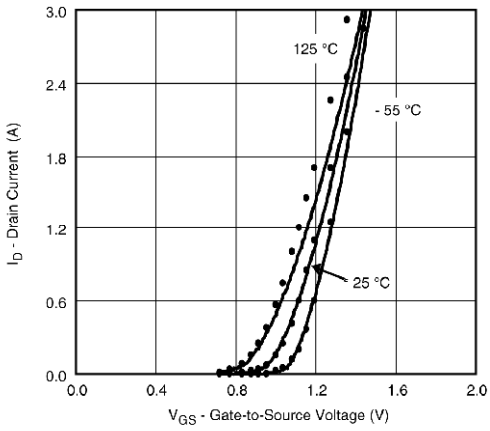
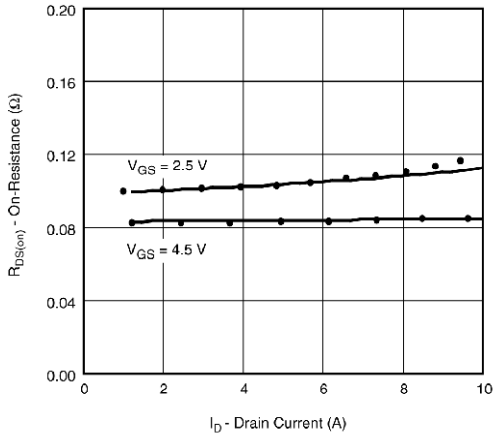
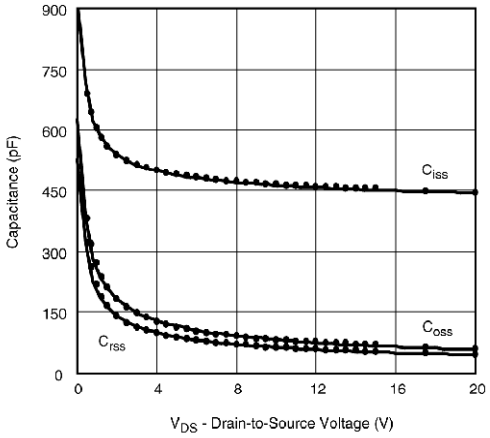
COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C UNLESS OTHERWISE NOTED)

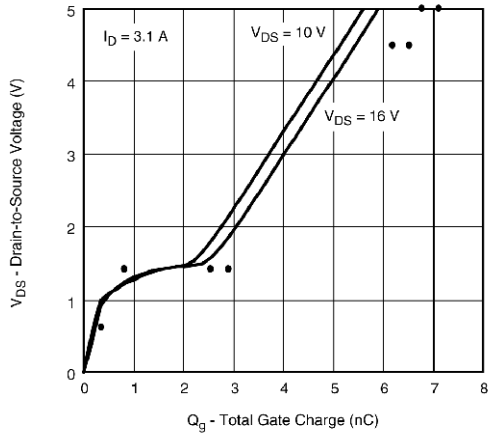
P-Channel MOSFET

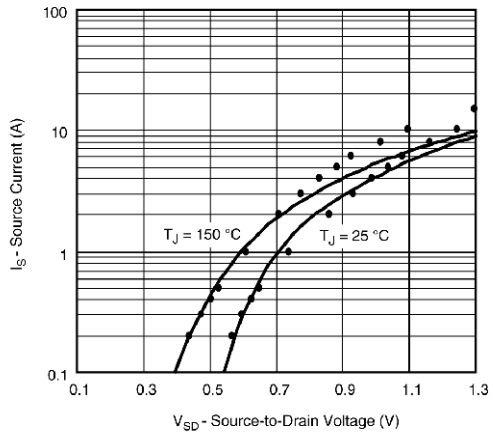












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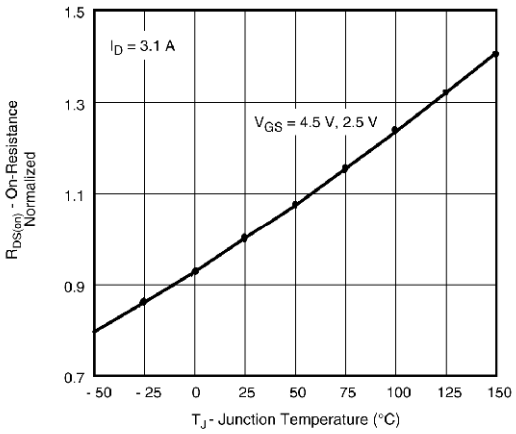
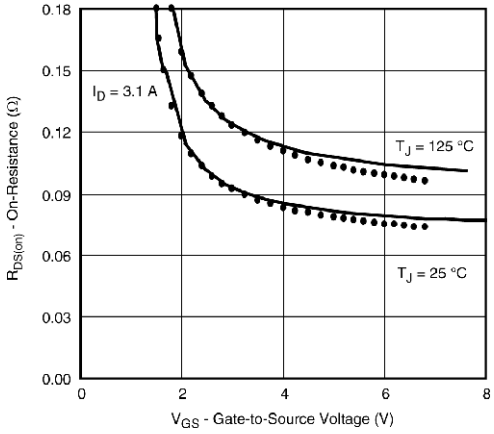
COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C UNLESS OTHERWISE NOTED)

P-Channel MOSFET





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